

Correction to High-Performance Field Effect Transistors from Solution Processed Carbon Nanotubes

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References 12 and 28 were incomplete in the published article. They are corrected below as references 1 and 2, respectively.

REFERENCES AND NOTES

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2. Stokes, P.; Khondaker, S. I. High Quality Solution Processed Carbon Nanotube Transistors Assembled by Dielectrophoresis. *Appl. Phys. Lett.* **2010**, *96*, 083110.

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